

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application No.: Not yet assigned  
Applicants: Christian DUSSARRAT, et al.  
Filed Internationally: April 8, 2004  
US National: Herewith  
Title: METHODS FOR PRODUCING SILICON NITRIDE FILMS BY VAPOR-PHASE GROWTH  
TC/A.U: Unknown  
Examiner: Unknown  
Docket No.: Serie 6070  
Customer No.: 000040582

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Prior to an examination of the merits of the above-identified U.S. patent application under 37 C.F.R. § 1.115, please first amend the application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** begin on page 4 of this paper.

**Amendments to the Abstract** begin on page 8 of this paper.

**Remarks** begin on page 9 of this paper.

An **Appendix** including the Abstract is attached following page 9 of this paper.